UTC MPSA194 PNP EPITAXIAL PLANAR TRANSISTOR

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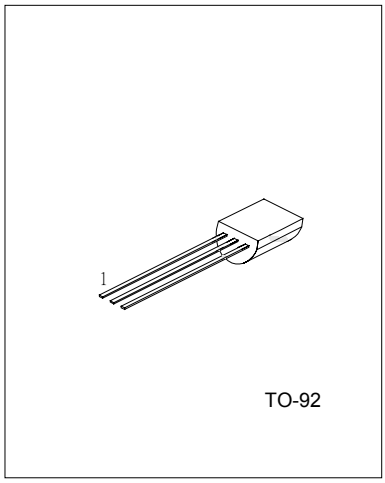

TO-92

1:EMITTER 2:BASE 3:COLLECTOR

DESCRIPTION

The MPSA194 is designed for high voltage low power switching applications especially for use in telephone and telecommunication circuits.

FEATURES

*Collector-Emitter Voltage:
V_{CEO}=400V
*Power Dissipation: 1.0W

APPLICATIONS

*Telephone circuit
*Telecommunication circuit

ABSOLUTE MAXIMUM RATINGS (Operating temperature range applies unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	400	V
Collector-emitter voltage	V_{CEO}	400	V
Emitter-base voltage	V_{EBO}	6	V
Collector dissipation(Ta=25°C)	Pc	1.0	W
Collector current	Ic	800	mA
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS(Tj=25°C,unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV_{CBO}	Ic=100μA,I_E=0	400			V
Collector-emitter breakdown voltage	BV_{CEO}	Ic=1mA,I_B=0	400			V
Collector cut-off current	I_{CBO}	V_{CB}=400V,I_E=0			10	μA
Collector cut-off current	I_{CEO}	V_{CB}=200V,V_{BE}=0			1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=6V,Ic=0			0.2	μA
DC current gain(note)	h_{FE}	V_{CE}=10V,Ic=1mA V_{CE}=10V,Ic=20mA V_{CE}=10V,Ic=80mA	50 50 40		 800	
Collector-emitter saturation voltage	V_{CE}(sat)	Ic=20mA,I_B=2mA Ic=80mA,I_B=4mA			0.2 1.2	V
Base-emitter saturation voltage	V_{BE}(sat)	Ic=20mA,I_B=2mA			0.9	V
Current Gain Bandwidth Porduct	fT	V_{CE}=20V,I_E=10mA, f=1MHz	10			MHz
Output capacitance	Cob	V_{CB}=20V,I_E=0, f=1MHz			30	pF